

DATA SHEET

BF820W; BF822W NPN high-voltage transistors

Product specification
Supersedes data of 1997 Jun 19
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN high-voltage transistors

BF820W; BF822W

FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

APPLICATIONS

- Telephony and professional communication equipment.

DESCRIPTION

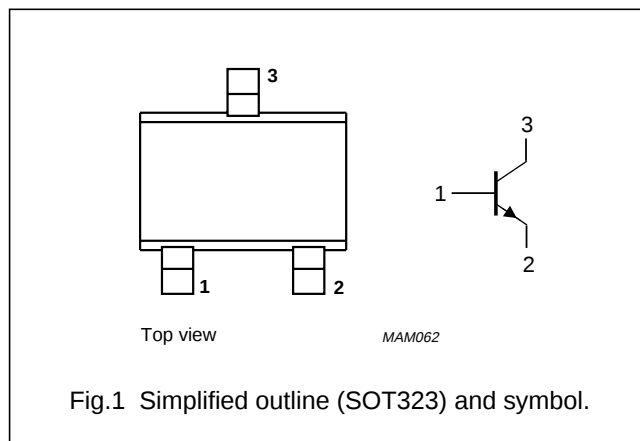
NPN high-voltage transistor in a SOT323 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BF820W	1Vt
BF822W	1Wt

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BF820W		–	300	V
	BF822W		–	250	V
V_{CEO}	collector-emitter voltage	open base			
	BF820W		–	300	V
	BF822W		–	250	V
I_{CM}	peak collector current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	–	200	mW
h_{FE}	DC current gain	$I_C = 25\text{ mA}; V_{CE} = 20\text{ V}$	50	–	
C_{re}	feedback capacitance	$I_C = i_c = 0; V_{CB} = 30\text{ V}; f = 1\text{ MHz}$	–	1.6	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	60	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage BF820W BF822W	open emitter	–	300	V
			–	250	V
V_{CEO}	collector-emitter voltage BF820W BF822W	open base	–	300	V
			–	250	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	50	mA
I_{CM}	peak collector current		–	100	mA
I_{BM}	peak base current		–	50	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 200\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 200\text{ V}$; $T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 5\text{ V}$	–	50	nA
h_{FE}	DC current gain	$I_C = 25\text{ mA}$; $V_{CE} = 20\text{ V}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 30\text{ mA}$; $I_B = 5\text{ mA}$; note 1	–	600	mV
C_{re}	feedback capacitance	$I_C = I_C = 0$; $V_{CB} = 30\text{ V}$; $f = 1\text{ MHz}$	–	1.6	pF
f_T	transition frequency	$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$	60	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ μs}$; $\delta \leq 0.02$.

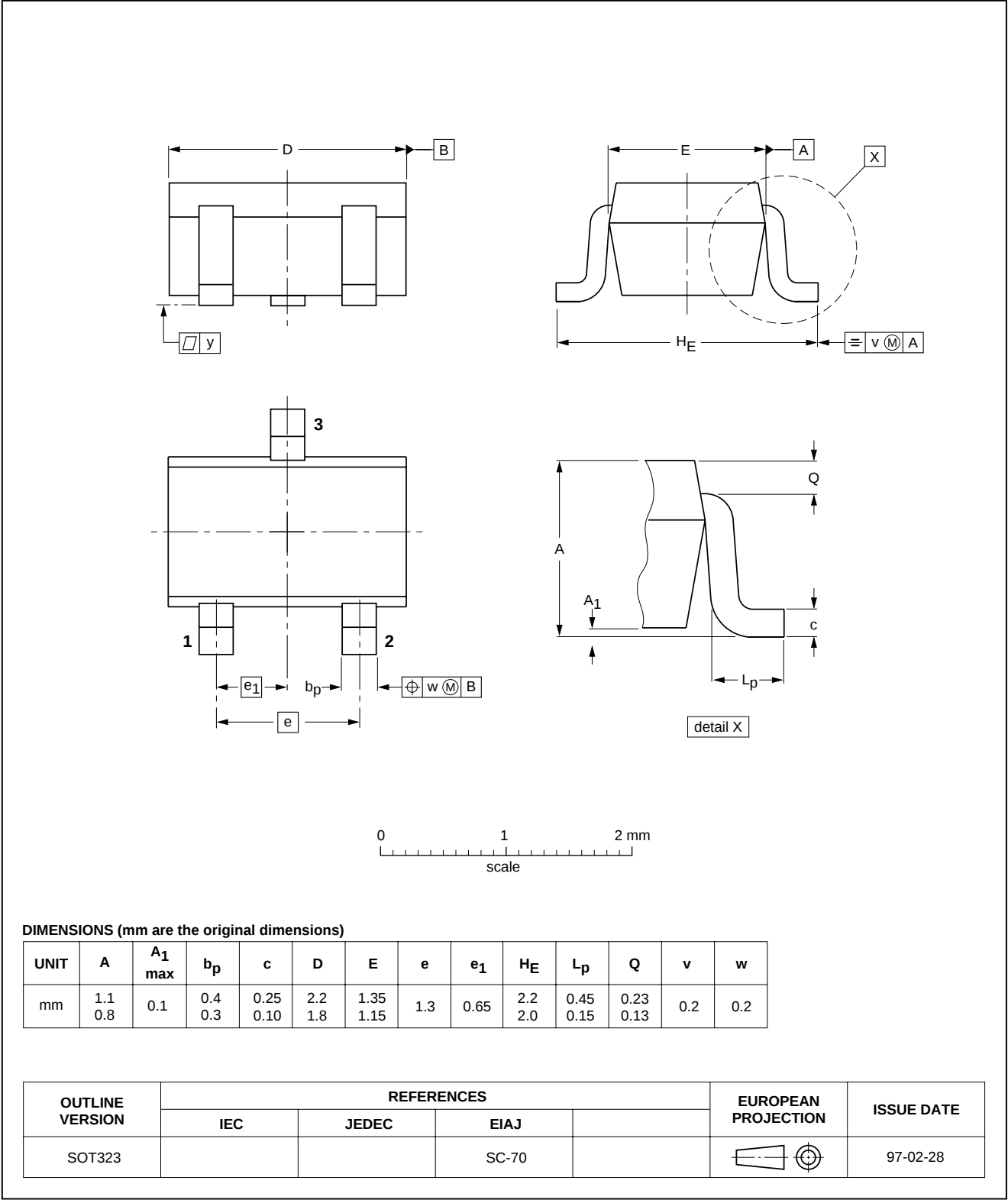
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NOTES

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NOTES

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